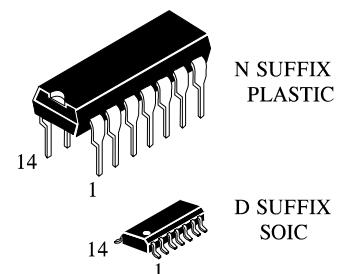


QUAD 2-INPUT NAND SCHMITT TRIGGERS

High-Voltage Silicon-Gate CMOS

The IW4093B consists of four Schmitt-trigger circuits. Each circuit functions as a two-input NAND gate with Schmitt-trigger action on both inputs. The gate switches at different points for positive- and negative-going signals. The difference between the positive voltage (V_P) and the negative voltage (V_N) is defined as hysteresis voltage (V_H) (see Fig.1).

- Operating Voltage Range: 3.0 to 18 V
- Maximum input current of 1 μ A at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package temperature range):
 - 1.0 V min @ 5.0 V supply
 - 2.0 V min @ 10.0 V supply
 - 2.5 V min @ 15.0 V supply

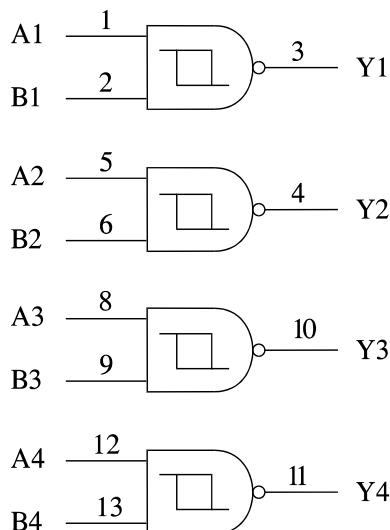


ORDERING INFORMATION

IW4093BN Plastic
IW4093BD SOIC

$T_A = -55^\circ$ to 125° C for all packages

LOGIC DIAGRAM



PIN 14 = V_{CC}
PIN 7 = GND

PIN ASSIGNMENT

A1	1 ●	14	V_{CC}
B1	2	13	B4
Y1	3	12	A4
Y2	4	11	Y4
A2	5	10	Y3
B2	6	9	B3
GND	7	8	A3

FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +20	V
V_{IN}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V_{OUT}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I_{IN}	DC Input Current, per Pin	± 10	mA
P_D	Power Dissipation in Still Air, Plastic DIP+ SOIC Package+	750 500	mW
P_D	Dissipation per Output Transistor	100	mW
T _{tsg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

+Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: : - 7 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	3.0	18	V
V_{IN}, V_{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T _A	Operating Temperature, All Package Types	-55	+125	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range $GND \leq (V_{IN} \text{ or } V_{OUT}) \leq V_{CC}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS(Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{cc} V	Guaranteed Limit			Unit
				≥-55°C	25°C	≤125 °C	
V _{T+min}	Minimum Positive-Going Input Threshold Voltage	Input on terminals A or B; other inputs to V _{cc}	5.0	2.2	2.2	2.2	V
			10	4.6	4.6	4.6	
V _{T+max}	Maximum Positive-Going Input Threshold Voltage	Input on terminals A or B; other inputs to V _{cc}	15	6.8	6.8	6.8	V
			5.0	2.6	2.6	2.6	
V _{T+max}	Maximum Positive-Going Input Threshold Voltage	Input on terminals A and B; other inputs to V _{cc}	10	5.6	5.6	5.6	V
			15	6.3	6.3	6.3	
V _{T-min}	Minimum Negative-Going Input Threshold Voltage	Input on terminals A or B; other inputs to V _{cc}	5.0	3.6	3.6	3.6	V
			10	7.1	7.1	7.1	
V _{T-min}	Minimum Negative-Going Input Threshold Voltage	Input on terminals A and B; other inputs to V _{cc}	15	10.8	10.8	10.8	V
			5.0	4	4	4	
V _{T-max}	Maximum Negative-Going Input Threshold Voltage	Input on terminals A or B; other inputs to V _{cc}	10	8.2	8.2	8.2	V
			15	12.7	12.7	12.7	
V _{Hmin} Note	Minimum Hysteresis Voltage	Input on terminals A or B; other inputs to V _{cc}	5.0	0.9	0.9	0.9	V
			10	2.5	2.5	2.5	
V _{Hmin} Note	Minimum Hysteresis Voltage	Input on terminals A and B; other inputs to V _{cc}	15	4	4	4	V
			5.0	1.4	1.4	1.4	
V _{Hmax} Note	Maximum Hysteresis Voltage	Input on terminals A or B; other inputs to V _{cc}	10	3.4	3.4	3.4	V
			15	4.8	4.8	4.8	
V _{Hmax} Note	Maximum Hysteresis Voltage	Input on terminals A and B; other inputs to V _{cc}	5.0	3.2	3.2	3.2	V
			10	6.6	6.6	6.6	
I _{IN}	Maximum Input Leakage Current	V _{IN} = GND or V _{cc}	15	9.6	9.6	9.6	μA
			5.0	1.6	1.6	1.6	
			10	3.4	3.4	3.4	
			15	5	5	5	
			5.0	1.6	1.6	1.6	
			10	3.4	3.4	3.4	
			15	5	5	5	

DC ELECTRICAL CHARACTERISTICS(Voltages Referenced to GND) - continued

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				≥-55°C	25°C	≤125 °C	
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{IN} = GND or V _{CC}	5.0 10 15 20	1 2 4 20	1 2 4 20	30 60 120 600	µA
I _{OL}	Minimum Output Low (Sink) Current	V _{IN} = GND or V _{CC} U _{OL} =0.4 V U _{OL} =0.5 V U _{OL} =1.5 V	5.0 10 15	0.64 1.6 4.2	0.51 1.3 3.4	0.36 0.9 2.4	mA
I _{OH}	Minimum Output High (Source) Current	V _{IN} = GND or V _{CC} U _{OH} =2.5 V U _{OH} =4.6 V U _{OH} =9.5 V U _{OH} =13.5 V	5.0 5.0 10 15	-2.0 -0.64 -1.6 -4.2	-1.6 -0.51 -1.3 -3.4	-1.15 -0.36 -0.9 -2.4	mA
V _{OH}	Minimum High-Level Output Voltage	V _{IN} =GND or V _{CC}	5.0 10 15	4.95 9.95 14.95	4.95 9.95 14.95	4.95 9.95 14.95	V
V _{OL}	Maximum Low-Level Output Voltage	V _{IN} = V _{CC}	5.0 10 15	0.05 0.05 0.05	0.05 0.05 0.05	0.05 0.05 0.05	V

Note. V_Hmin>(V_{T+}min)-(V_{T-}max); V_Hmax=(V_{T+}max)+(V_{T-}min).

AC ELECTRICAL CHARACTERISTICS(C_L=50pF, R_L=200kΩ, Input t_r=t_f=20 ns)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			≥-55 °C	25°C	≤125 °C	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Output Y (Figure 2)	5.0 10 15	380 180 130	380 180 130	760 360 260	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figure 2)	5.0 10 15	200 100 80	200 100 80	400 200 160	ns
C _{IN}	Maximum Input Capacitance	-		7.5		pF

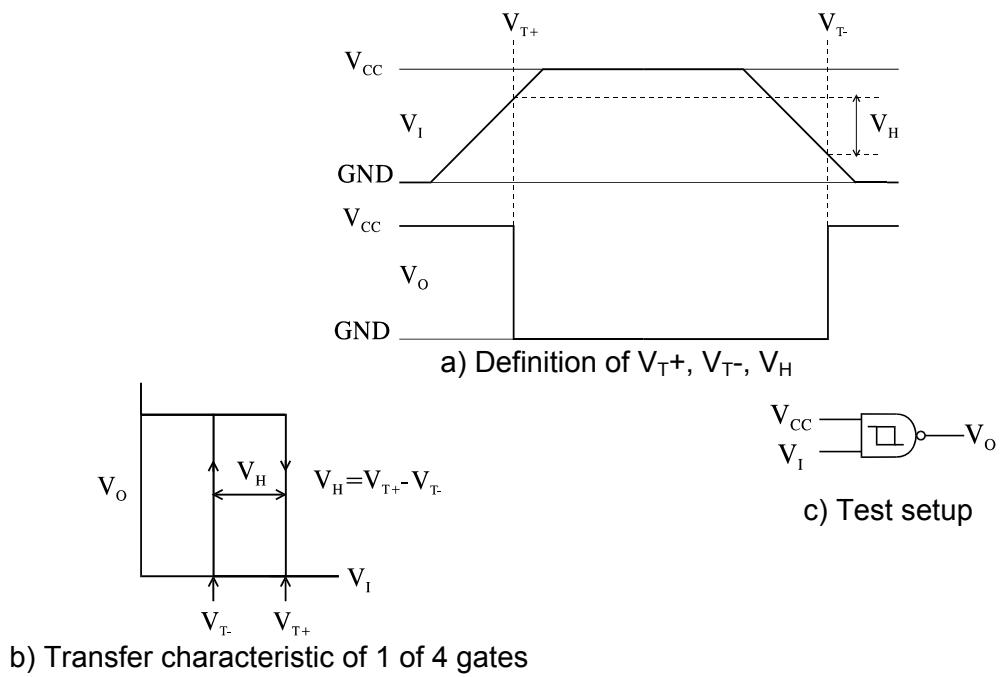


Figure 1. Hysteresis definition, characteristic, and test setup

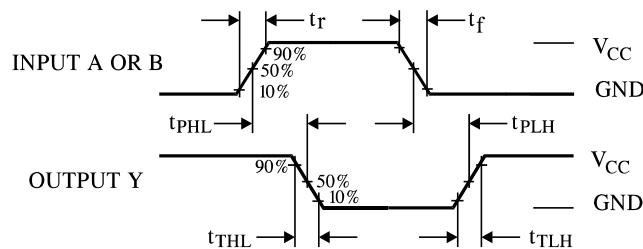


Figure 2. Switching Waveforms

EXPANDED LOGIC DIAGRAM (1/4 of the Device)

